

52. (New) The method of claim 50, wherein the reducing compound is selected from a group consisting of SiH<sub>4</sub>, B<sub>2</sub>H<sub>6</sub>, NH<sub>3</sub>, and combinations thereof.

53. (New) The method of claim 50, wherein the adhesion layer is deposited within a first processing chamber and the barrier layer is deposited within a second processing chamber.

54. (New) The method of claim 53, wherein the copper is deposited in a third processing chamber and the first, second and third processing chambers are each disposed about a common mainframe.

#### REMARKS

Claims 1-25 are pending in the application and are subject to a restriction and/or election requirement. Applicants elect prosecution on the merits of Group 1 (claims 1-19) with traverse. Furthermore, Applicants have added new claims 26-54 to recite additional aspects of the invention. New claims 26-54 are directed to the subject matter of Group 1, and no new matter has been added.

The Examiner restricted claims 1-25 to one of the following inventions under U.S.C. §121:

- I. Claims 1-19, drawn to process for forming a stacked barrier layer; and
- II. Claims 20-25, drawn to a processing system for forming a stacked barrier layer.

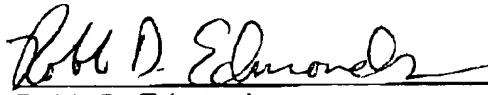
The Examiner states that Groups I and II are related as process and apparatus for its practice. The Examiner also states that that Groups I and II are distinct, each from the other because the apparatus as claimed can be used to practice another and materially different process, such as etching.

Applicants respectfully traverse this restriction. Claim 20 recites "means" for practicing the functions of the method defined by claims 1-19, and claims 21-25 recite a

program for performing that method. No showing has been made that the apparatus for performing those method steps or the program for performing that method could have been used in an etching process. Accordingly, withdrawal of the restriction and prosecution of all claims 1-54 is respectfully requested.

If the Examiner believes any unresolved issues still exist, please telephone Robb Edmonds at (713) 623-4844 so that appropriate arrangements can be made for resolving such issues as expeditiously as possible.

Respectfully submitted,



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## APPENDIX

1. (Amended) A method for forming a stacked barrier layer on a substrate disposed in a processing chamber, [said method] comprising:
  - serially exposing said substrate to first and second reactive gases to form an adhesion layer; and
  - serially exposing said adhesion layer to third and fourth reactive gases to form a barrier layer adjacent to said adhesion layer.